

## UNISONIC TECHNOLOGIES CO., LTD

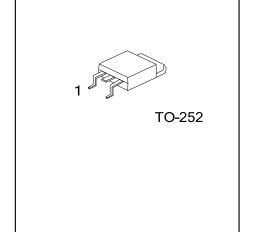
UTT60P03 Preliminary Power MOSFET

# -60A, -30V, P-CHANNEL POWER MOSFETS

## ■ DESCRIPTION

The UTC **UTT60P03** is a P-channel power MOSFET using UTC's advanced technology to provide the customers with high switching speed and a minimum on-state resistance and it can also withstand high energy in the avalanche.

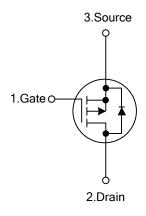
This UTC **UTT60P03** is suitable for switching converters, motor drivers, switching regulators and relay drivers.



#### **■ FEATURES**

- \* V<sub>DS</sub> = -60V
- \*  $I_D = -30A$
- \*  $R_{DS(ON)}$ =0.027 $\Omega$  @  $V_{GS}$ =-10V,  $I_D$ =-60A
- \* High Switching Speed

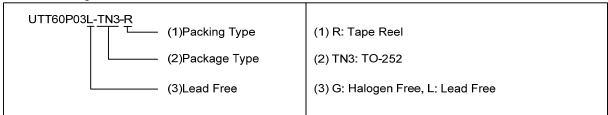
#### ■ SYMBOL



#### ■ ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Daakina	
Lead Free	Halogen Free	Package		2	3	Packing	
UTT60P03L-TN3-R	UTT60P03G-TN3-R	TO-252	G	D	S	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



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## ■ **ABSOLUTE MAXIMUM RATINGS** (T<sub>C</sub>=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage (Note 2)		V <sub>DSS</sub>	-30	V
Gate-Source Voltage		$V_{GSS}$	±20	V
Drain Current	Continuous	I <sub>D</sub>	-60	Α
	Pulsed (Note 2)	I <sub>DM</sub>	240	Α
Power Dissipation		D	45	W
Derate Above 25°C		P <sub>D</sub>	0.36	W/°C
Junction Temperature		TJ	+150	°C
Storage Temperature		T <sub>STG</sub>	-55~+150	°C

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

## **■ THERMAL CHARACTERISTICS**

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$\theta_{JA}$	110	°C/W
Junction to Case	$\theta_{JC}$	2.73	°C/W

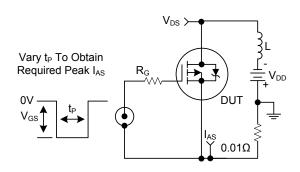
<sup>2.</sup> Repetitive rating: Pulse width limited by maximum junction temperature

## ■ ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C, unless otherwise specified)

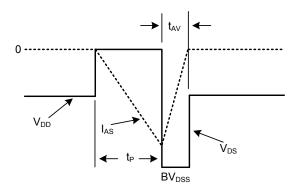
PARAMETER		SYMBOL	TEST CONDITIONS			TYP	MAX	UNIT
OFF CHARACTERISTICS	'				l.		l.	
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V		-30			V
Drain-Source Leakage Current		I <sub>DSS</sub>	V <sub>DS</sub> =Rated BV <sub>DSS</sub> , V <sub>GS</sub> =0V				-1	
			V <sub>DS</sub> =0.8×Rated BV <sub>DSS</sub> , T <sub>C</sub> =150°C				-50	μA
Gate- Source Leakage	Forward		V <sub>GS</sub> =+20V V <sub>GS</sub> =-20V				+100	nΑ
Current	Reverse	$I_{GSS}$					-100	nΑ
ON CHARACTERISTICS								
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250\mu A$		-2		-4	V
Static Drain-Source On-State Resistance (Note)		R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-60A				0.027	Ω
DYNAMIC PARAMETERS							•	
Input Capacitance		C <sub>ISS</sub>				3000		pF
Output Capacitance		Coss	V <sub>GS</sub> =0V, V <sub>DS</sub> =-25V, f=1.0MHz			1500		pF
Reverse Transfer Capacitance		$C_{RSS}$				525		pF
SWITCHING PARAMETERS	S						-	
Total Gate Charge		$Q_{G}$	V <sub>GS</sub> =0 ~ -20V	V = 04V I ~ 00A		190	230	nC
Gate Charge at 10V		Q <sub>G(-10)</sub>	V <sub>GS</sub> =0 ~ -10V	V <sub>DD</sub> =-24V, I <sub>D</sub> ≈-60A, -R <sub>L</sub> =0.4Ω, I <sub>G(REF)</sub> =-3mA		100	120	nC
Threshold Gate Charge		$Q_{G(TH)}$	V <sub>GS</sub> =0 ~ -2V	17L-0.422, IG(REF)3IIIA		7.5	9	nC
Turn-On Time		t <sub>ON</sub>					140	ns
Turn-ON Delay Time		$t_{D(ON)}$	V <sub>DD</sub> =15V, V <sub>GS</sub> =-10V, I <sub>D</sub> ≈60A, R <sub>L</sub> =0.25Ω, R <sub>G</sub> =2.5Ω			20		ns
Rise Time	Rise Time Turn-OFF Delay Time					75		ns
Turn-OFF Delay Time						35		ns
Fall-Time		$t_{F}$				40		ns
Turn-Off Time		$t_{OFF}$					115	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Drain-Source Diode Forward (Note )	l Voltage	$V_{\text{SD}}$	I <sub>SD</sub> =-60A				-1.75	٧
Body Diode Reverse Recove	ery Time	t <sub>RR</sub>	I <sub>SD</sub> =-60A, I <sub>SD</sub> /dt=100A/μs				200	ns

Note: Pulse test: pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .

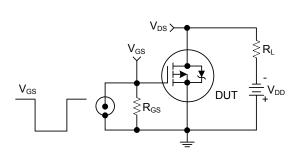
## **■ TEST CIRCUITS AND WAVEFORMS**



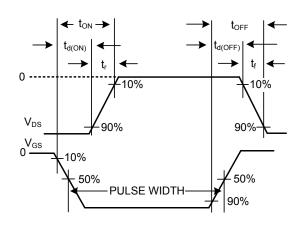
**Unclamped Energy Test Circuit** 



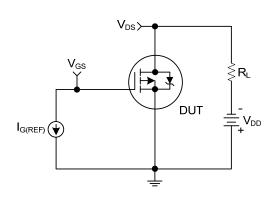
**Unclamped Energy Waveform** 



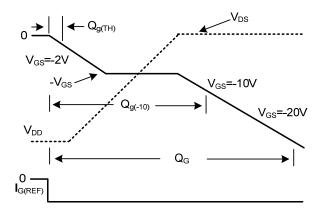
Switching Time Test Circuit



Resistive Switching Waveforms



Gate Charge Test Circuit



Gate Charge Waveforms

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